PowerMOS transistor

BUK446-1000A
BUK446-1000B

T-39-09

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic full-pack envelope.
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK446	-1000A	-1000B	
V_{DS}	Drain-source voltage	1000	1000	V
I_D	Drain current (DC)	1.7	1.5	A
P_{tot}	Total power dissipation	30	30	W
$R_{DS(ON)}$	Drain-source on-state resistance	4	5	Ω

MECHANICAL DATA

Dimensions in mm

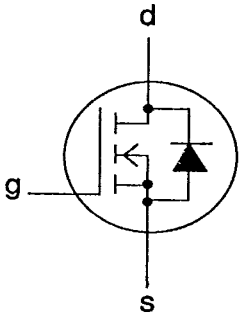
Net Mass: 2g

Pinning:

1 = Gate

2 = Drain

3 = Source



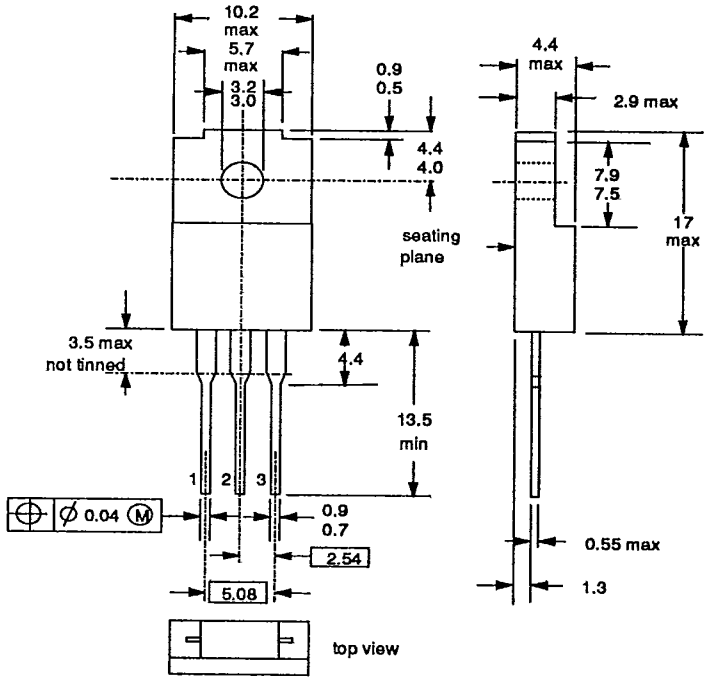


Fig.1 SOT-186; The seating plane is electrically isolated from all terminals.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Accessories supplied on request: refer to Mounting instructions for F-pack envelopes.

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DS}	Drain-source voltage	-	-	1000		V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	1000		V
$\pm V_{GS}$	Gate-source voltage	-	-	30		V
				-1000A	-1000B	
I_D	Drain current (DC)	T_{hs} = 25 °C	-	1.7	1.5	A
I_D	Drain current (DC)	T_{hs} = 100 °C	-	1.1	1.0	A
I_{DM}	Drain current (pulse peak value)	T_{hs} = 25 °C	-	6.8	6	A
P_{tot}	Total power dissipation	T_{hs} = 25 °C	-	30		W
T_{stg}	Storage temperature	-	- 55	150		°C
T_j	Junction Temperature	-	-	150		°C

THERMAL RESISTANCES

From junction to heatsink	with heatsink compound	$R_{th\ j\text{-}hs}$ = 4.16 K/W
From junction to ambient	-	$R_{th\ j\text{-}a}$ = 55 K/W

STATIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA	1000	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1000 V; V_{GS} = 0 V; T_j = 25 °C	-	2	20	μA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1000 V; V_{GS} = 0 V; T_j =125 °C	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	V_{GS} = ±30 V; V_{DS} = 0 V	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 1.5 A **BUK446-1000A**	-	3.5	4.0	Ω
		BUK446-1000B	-	4.5	5.0	Ω

DYNAMIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 1.5 A	3.0	4.3	-	S
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	1000	1250	pF
C_{oss}	Output capacitance		-	80	120	pF
C_{rss}	Feedback capacitance		-	30	50	pF
$t_{d\ on}$	Turn-on delay time	V_{DD} = 30 V; I_D = 2.3 A;	-	10	25	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_{GS} = 50 Ω;	-	25	40	ns
$t_{d\ off}$	Turn-off delay time	R_{gen} = 50 Ω	-	130	150	ns
t_f	Turn-off fall time		-	40	60	ns
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

ISOLATION

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-	-	1500	V
C_{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	-	pF

REVERSE DIODE RATINGS AND CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	1.7	A
I_{DRM}	Pulsed reverse drain current	-	-	-	6.8	A
V_{SD}	Diode forward voltage	I_F = 1.7 A ; V_{GS} = 0 V	-	1.0	1.3	V
t_{rr}	Reverse recovery time	I_F = 1.7 A; -dI_F/dt = 100 A/µs;	-	1800	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = 0 V; V_R = 100 V	-	12	-	µC

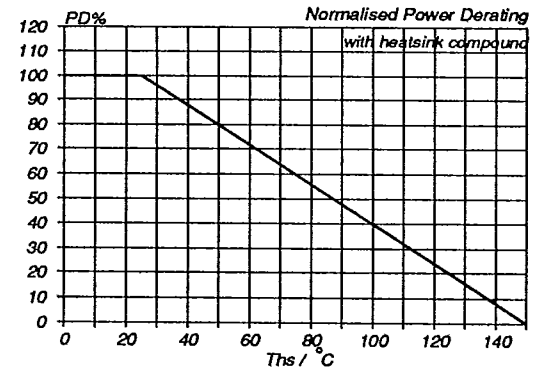

Fig.2. Normalised power dissipation.
PD% = 100·$P_D/P_{D\ 25\ °C}$ = f(T_{hs})

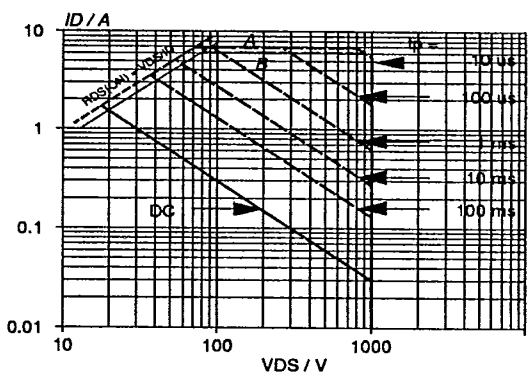

Fig.4. Safe operating area. T_{hs} = 25 °C
I_D & I_{DM} = f(V_{DS}); I_{DM} single pulse; parameter t_p

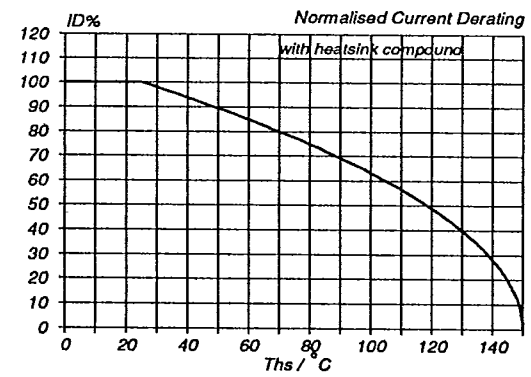

Fig.3. Normalised continuous drain current.
ID% = 100·$I_D/I_{D\ 25\ °C}$ = f(T_{hs}); conditions: $V_{GS} \geq$ 10 V

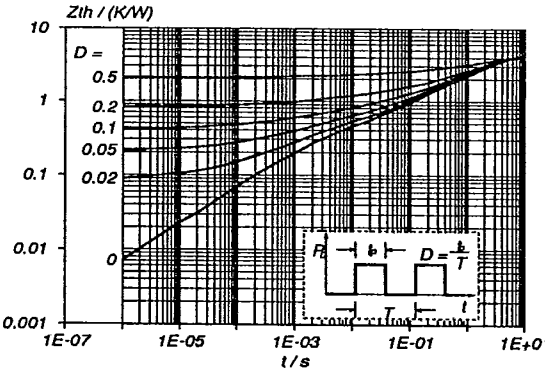

Fig.5. Transient thermal impedance.
$Z_{th\ j\text{-}hs}$ = f(t); parameter D = t_p/T

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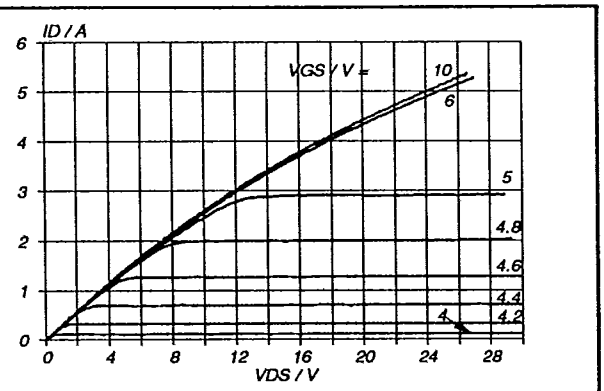

Fig.6.[1] Typical output characteristics, $T_j = 25$ °C. $I_D = f(V_{DS})$; parameter V_{GS}

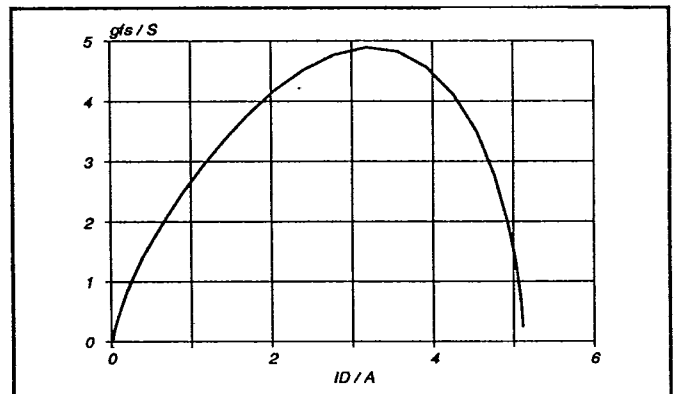

Fig.9. Typical transconductance, $T_j = 25$ °C. $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25$ V

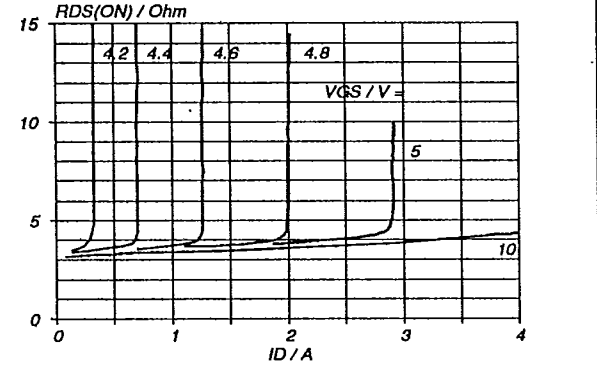

Fig.7. Typical on-state resistance, $T_j = 25$ °C. $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

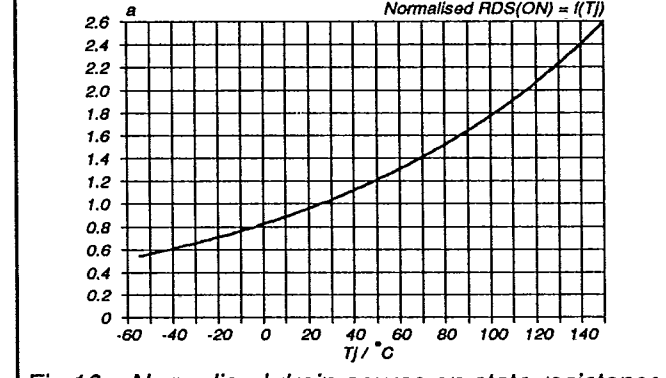

Fig.10. Normalised drain-source on-state resistance. $a = R_{DS(ON)}/R_{DS(ON)25\,°C} = f(T_j)$; $I_D = 1.5$ A; $V_{GS} = 10$ V

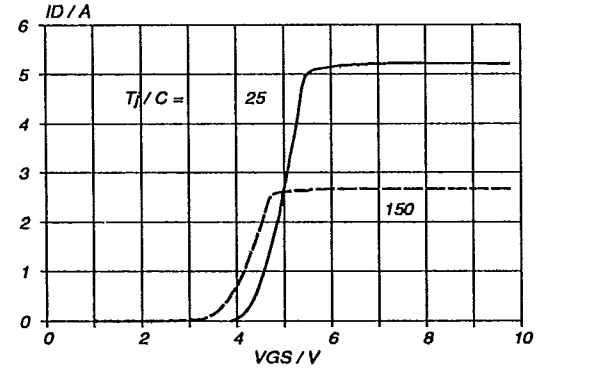

Fig.8. Typical transfer characteristics. $I_D = f(V_{GS})$; conditions: $V_{DS} = 25$ V; parameter T_j

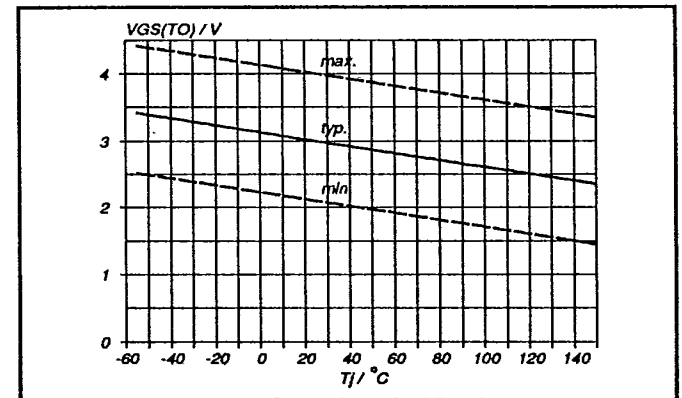

Fig.11. Gate threshold voltage. $V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = V_{GS}$

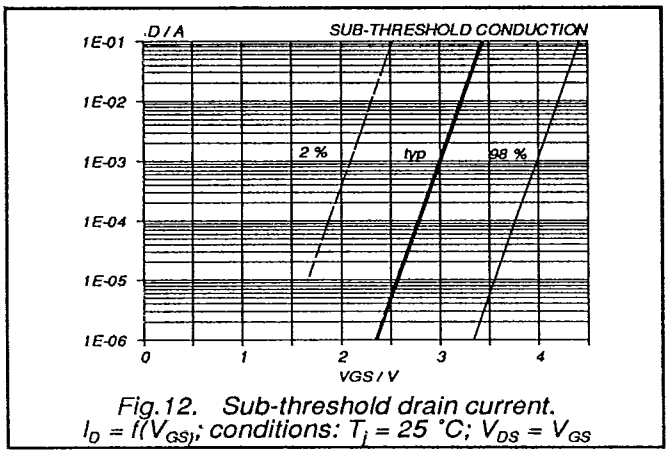

Fig.12. Sub-threshold drain current.
$I_D = f(V_{GS})$; *conditions:* $T_j = 25$ °C; $V_{DS} = V_{GS}$

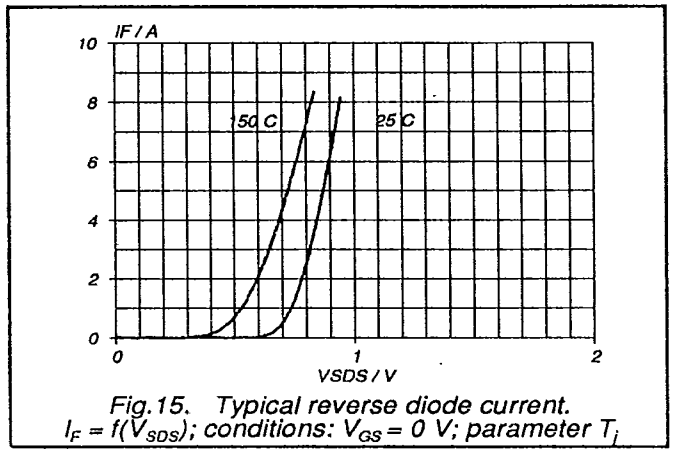

Fig.15. Typical reverse diode current.
$I_F = f(V_{SDS})$; *conditions:* $V_{GS} = 0$ V; *parameter* T_j

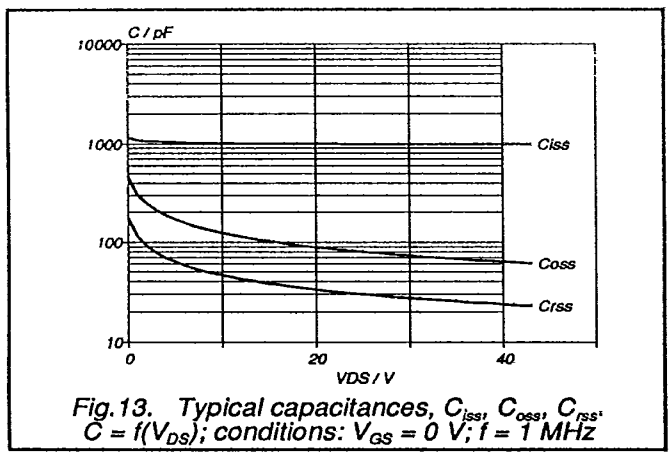

Fig.13. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; *conditions:* $V_{GS} = 0$ V; $f = 1$ MHz

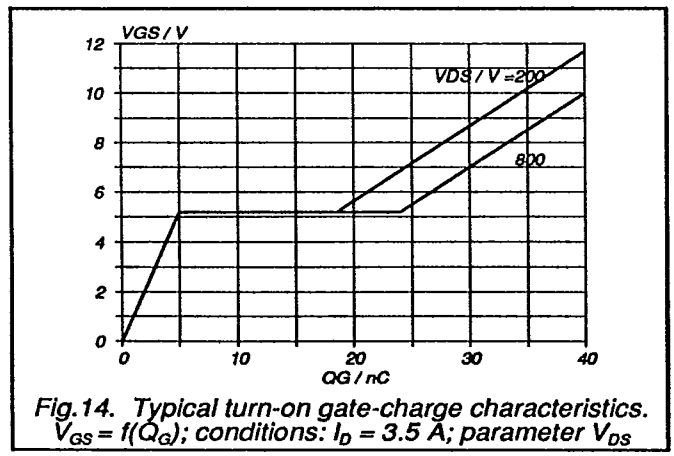

Fig.14. Typical turn-on gate-charge characteristics.
$V_{GS} = f(Q_G)$; *conditions:* $I_D = 3.5$ A; *parameter* V_{DS}